

MITSUBISHI IGBT MODULES

# CM200DU-24NFH

HIGH POWER SWITCHING USE

## CM200DU-24NFH



- IC ..... 200A
- VCES ..... 1200V
- Insulated Type
- 2-elements in a pack

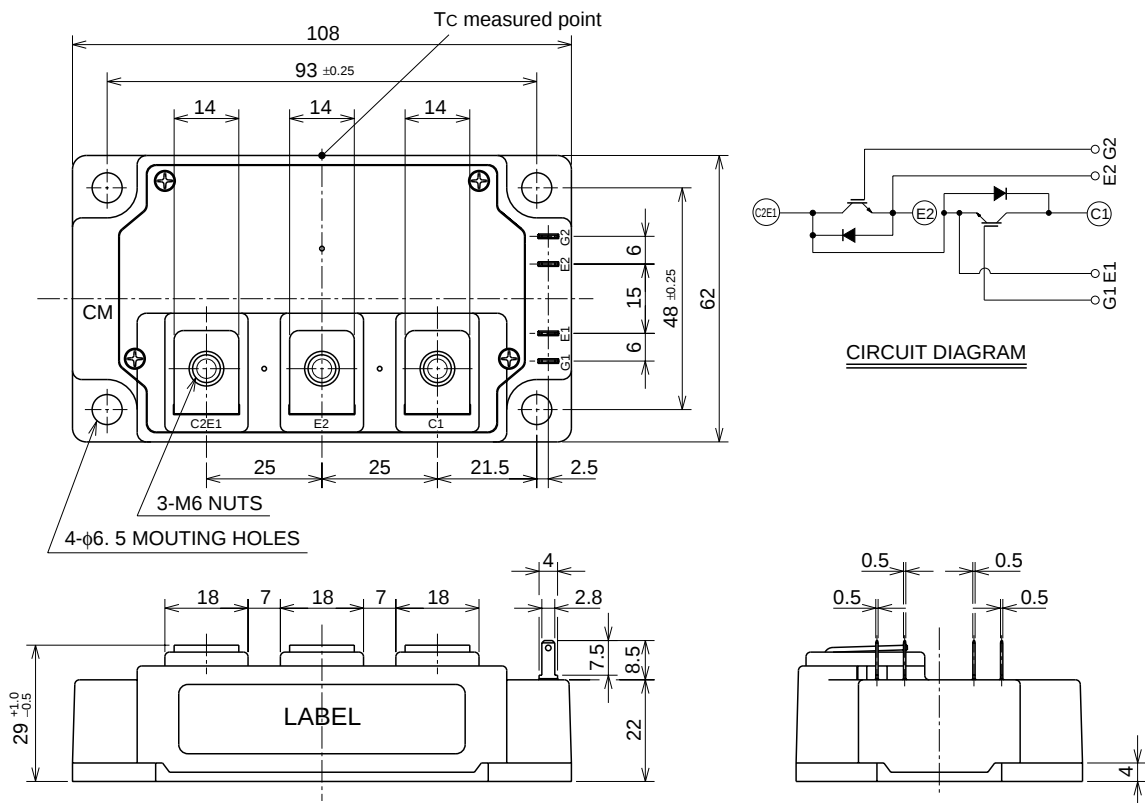
## APPLICATION

High frequency switching use (30kHz to 60kHz).

Gradient amplifier, Induction heating, power supply, etc.

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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### MAXIMUM RATINGS (Tj = 25°C)

| Symbol                    | Parameter                     | Conditions                             | Ratings    | Unit  |
|---------------------------|-------------------------------|----------------------------------------|------------|-------|
| V <sub>CE</sub>           | Collector-emitter voltage     | G-E Short                              | 1200       | V     |
| V <sub>GE</sub>           | Gate-emitter voltage          | C-E Short                              | ±20        | V     |
| I <sub>C</sub>            | Collector current             | Operation (Note 2)                     | 200        | A     |
| I <sub>CM</sub>           |                               | Pulse (Note 2)                         | 400        | A     |
| I <sub>E</sub> (Note 1)   | Emitter current               | Operation (Note 2)                     | 200        | A     |
| I <sub>EM</sub> (Note 1)  |                               | Pulse (Note 2)                         | 400        | A     |
| P <sub>C</sub> (Note 3)   | Maximum collector dissipation | T <sub>C</sub> = 25°C                  | 830        | W     |
| P <sub>C</sub> ' (Note 3) | Maximum collector dissipation | T <sub>C</sub> ' = 25°C*4              | 1300       | W     |
| T <sub>j</sub>            | Junction temperature          |                                        | −40 ~ +150 | °C    |
| T <sub>stg</sub>          | Storage temperature           |                                        | −40 ~ +125 | °C    |
| V <sub>iso</sub>          | Isolation voltage             | Main Terminal to base plate, AC 1 min. | 2500       | V     |
| —                         | Mounting torque               | Main Terminal M6                       | 3.5 ~ 4.5  | N • m |
| —                         |                               | Mounting holes M6                      | 3.5 ~ 4.5  | N • m |
| —                         | Weight                        | Typical value                          | 400        | g     |

### ELECTRICAL CHARACTERISTICS (Tj = 25°C)

| Symbol                   | Parameter                                     | Test conditions                                                                                                                                                                  | Limits |      |         | Unit |
|--------------------------|-----------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|------|---------|------|
|                          |                                               |                                                                                                                                                                                  | Min.   | Typ. | Max.    |      |
| I <sub>CES</sub>         | Collector cutoff current                      | V <sub>CE</sub> = V <sub>CE</sub> , V <sub>GE</sub> = 0V                                                                                                                         | —      | —    | 1       | mA   |
| V <sub>GE(th)</sub>      | Gate-emitter threshold voltage                | I <sub>C</sub> = 20mA, V <sub>CE</sub> = 10V                                                                                                                                     | 4.5    | 6    | 7.5     | V    |
| I <sub>GES</sub>         | Gate leakage current                          | V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V                                                                                                                        | —      | —    | 0.7     | μA   |
| V <sub>CE(sat)</sub>     | Collector-emitter saturation voltage (Note 4) | T <sub>j</sub> = 25°C                                                                                                                                                            | —      | 5.0  | 6.5     | V    |
|                          |                                               | T <sub>j</sub> = 125°C                                                                                                                                                           | —      | 5.0  | —       |      |
| C <sub>ies</sub>         | Input capacitance                             | V <sub>CE</sub> = 10V<br>V <sub>GE</sub> = 0V                                                                                                                                    | —      | —    | 32      | nF   |
| C <sub>oes</sub>         | Output capacitance                            |                                                                                                                                                                                  | —      | —    | 2.7     | nF   |
| C <sub>res</sub>         | Reverse transfer capacitance                  |                                                                                                                                                                                  | —      | —    | 0.6     | nF   |
| Q <sub>G</sub>           | Total gate charge                             | V <sub>CC</sub> = 600V, I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V                                                                                                             | —      | 900  | —       | nC   |
| t <sub>d(on)</sub>       | Turn-on delay time                            | V <sub>CC</sub> = 600V, I <sub>C</sub> = 200A<br>V <sub>GE1</sub> = V <sub>GE2</sub> = 15V<br>R <sub>G</sub> = 1.6Ω, Inductive load switching operation<br>I <sub>E</sub> = 200A | —      | —    | 300     | ns   |
| t <sub>r</sub>           | Turn-on rise time                             |                                                                                                                                                                                  | —      | —    | 80      | ns   |
| t <sub>d(off)</sub>      | Turn-off delay time                           |                                                                                                                                                                                  | —      | —    | 500     | ns   |
| t <sub>f</sub>           | Turn-off fall time                            |                                                                                                                                                                                  | —      | —    | 150     | ns   |
| t <sub>rr</sub> (Note 1) | Reverse recovery time                         |                                                                                                                                                                                  | —      | —    | 250     | ns   |
| Q <sub>rr</sub> (Note 1) | Reverse recovery charge                       |                                                                                                                                                                                  | —      | 7.5  | —       | μC   |
| V <sub>EC</sub> (Note 1) | Emitter-collector voltage                     | I <sub>E</sub> = 200A, V <sub>GE</sub> = 0V                                                                                                                                      | —      | —    | 3.5     | V    |
| R <sub>th(j-c)Q</sub>    | Thermal resistance*1                          | IGBT part (1/2 module)                                                                                                                                                           | —      | —    | 0.15    | °C/W |
| R <sub>th(j-c)R</sub>    |                                               | FWDi part (1/2 module)                                                                                                                                                           | —      | —    | 0.24    | °C/W |
| R <sub>th(c-f)</sub>     | Contact thermal resistance                    | Case to fin, Thermal compound Applied*2 (1/2 module)                                                                                                                             | —      | 0.04 | —       | °C/W |
| R <sub>th(j-c')Q</sub>   | Thermal resistance*4                          | IGBT part (1/2 module)                                                                                                                                                           | —      | —    | 0.095*3 | °C/W |
| R <sub>th(j-c')R</sub>   |                                               | FWDi part (1/2 module)                                                                                                                                                           | —      | —    | 0.14*3  | °C/W |
| R <sub>G</sub>           | External gate resistance                      |                                                                                                                                                                                  | 1.6    | —    | 16      | Ω    |

\*1 : T<sub>C</sub> measured point is shown in page OUTLINE DRAWING.

\*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

\*3 : If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

\*4 : T<sub>C</sub>' measured point is just under the chips.

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub> & Q<sub>rr</sub> represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

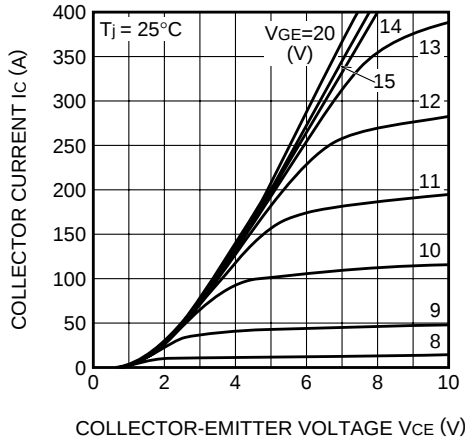
4. No short circuit capability is designed.

# CM200DU-24NFH

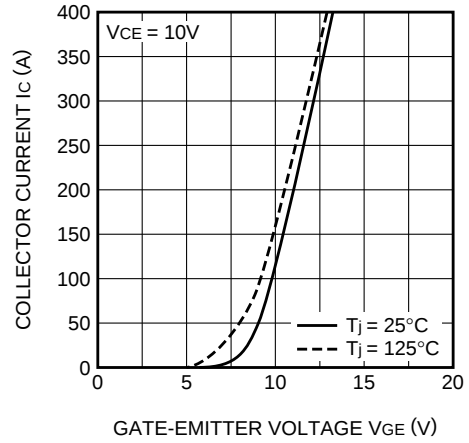
HIGH POWER SWITCHING USE

## PERFORMANCE CURVES

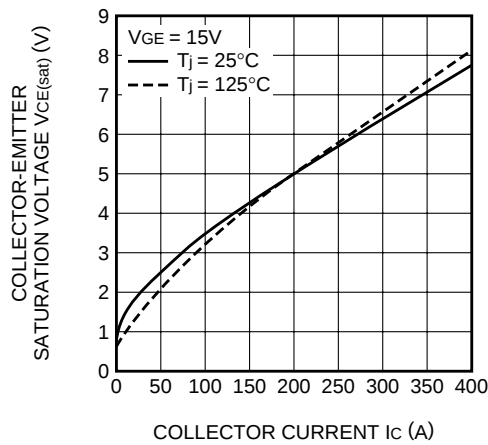
OUTPUT CHARACTERISTICS  
(TYPICAL)



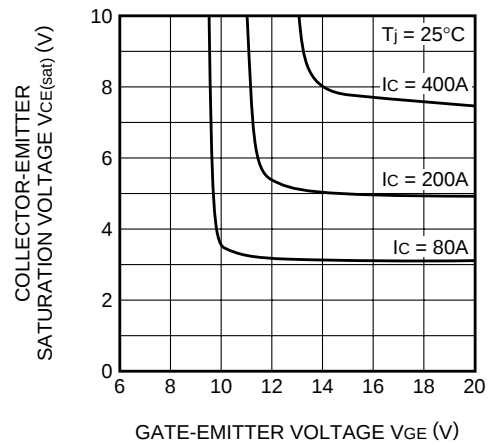
TRANSFER CHARACTERISTICS  
(TYPICAL)



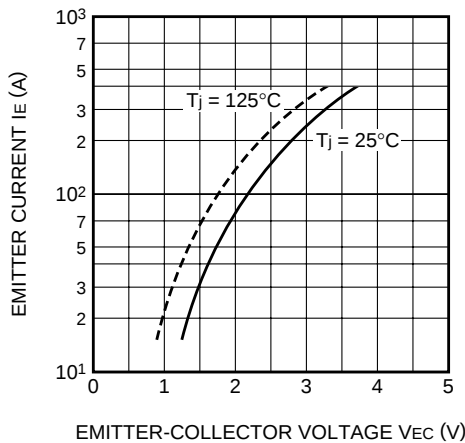
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



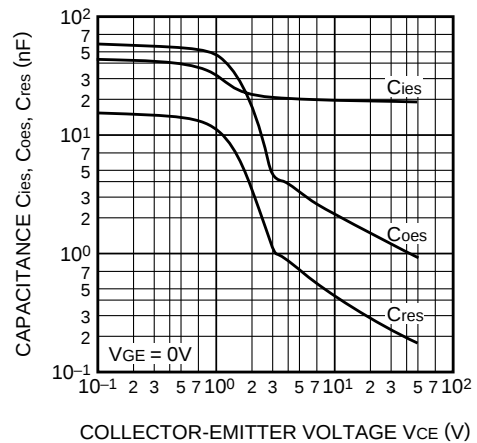
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



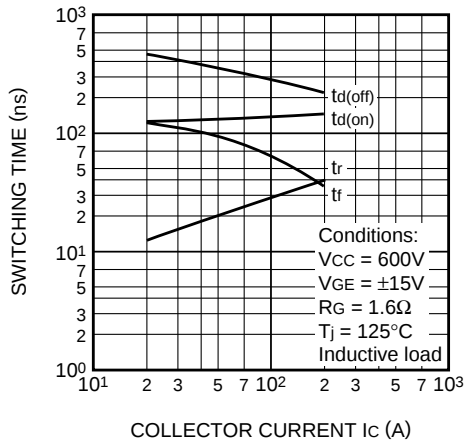
CAPACITANCE CHARACTERISTICS  
(TYPICAL)



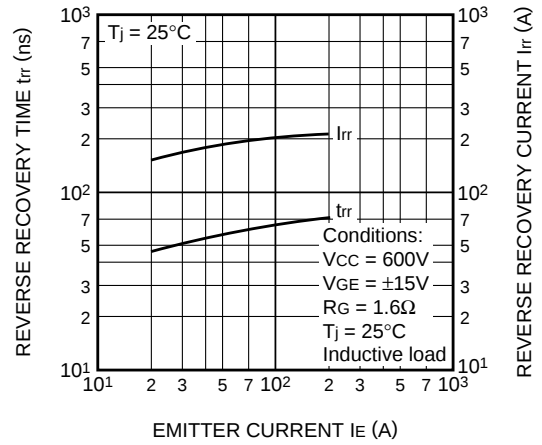
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HIGH POWER SWITCHING USE

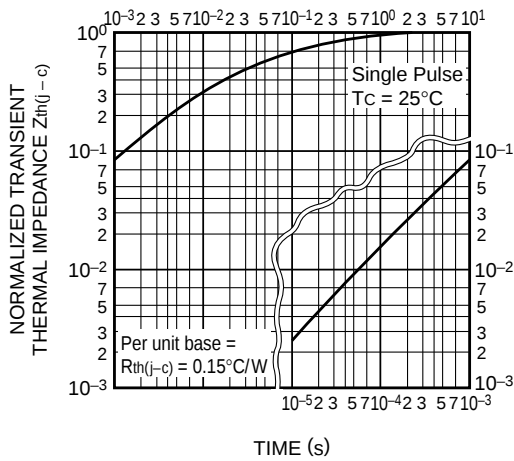
**HALF-BRIDGE  
SWITCHING TIME CHARACTERISTICS  
(TYPICAL)**



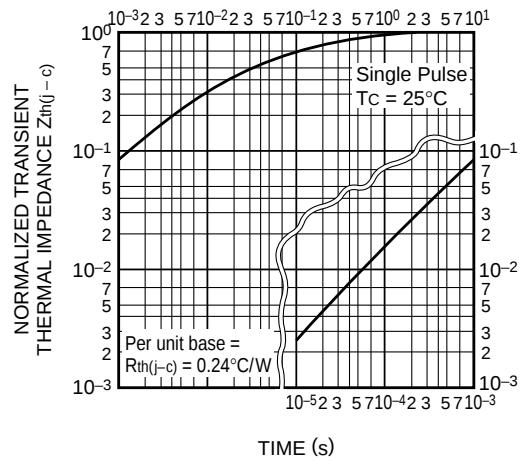
**REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE  
(TYPICAL)**



**TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(IGBT part)**



**TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(FWDi part)**



**GATE CHARGE CHARACTERISTICS  
(TYPICAL)**

